

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:)	Examiner: Not Yet Assigned
Name Neil M. Mackie et al)	Art Group: Not Yet Assigned
Serial No. Not Yet Assigned)	Att. Docket No.: MAT-12CIP
Filed: March 17, 2004)	Date: March 17, 2004
For: EFFLUENT PRESSURE CONTROL FOR USE IN A)	
PROCESSING SYSTEM)	

CERTIFICATE OF MAILING I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on March 17, 2004.

Signed:

Jay R Beyer

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a form 1449 including references cited in the parent application serial number 10/413,507 filed April 14, 2003 associated with this application. Copies of the references cited in the parent application may be found in the parent application. It is respectfully requested that the cited documents be considered and that the enclosed copies of the forms be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

- ☒ 37 C.F.R. § 1.97(b).
☐ 37 C.F.R. § 1.97(c). If so, then enclosed with this Information Disclosure Statement is one of the following:
 ☐ A certification pursuant to 37 C.F.R. § 1.97(e) or
 ☐ A check for \$_____ for the fee under 37 C.F.R. § 1.17(p).
☐ 37 C.F.R. § 1.97(d). If so, then enclosed with this Information Disclosure Statement are the following:
 (1) A certification pursuant to 37 C.F.R. § 1.97(e);
 (2) A petition requesting consideration of the Information Disclosure Statement; and
 (3) Please charge Deposit Account No. 19-1685 (Order No. MAT-12CIP) \$_____ for the fee under 37 C.F.R. § 1.17(i) for submission of the Information Disclosure Statement. (a duplicate copy of this sheet is enclosed)

If there are any additional charges, please charge Deposit Account No. 19-1685 (Order No. MAT-12CIP).

Respectfully submitted,

Jay R Beyer

Registration No. 39,907

Form 1449 (Modified)	Atty Docket No. MAT-12CIP	Serial No.: Not Yet Assigned
Information Disclosure Statement By Applicant	Applicants: Neil M. Mackie et al	
(Use Several Sheets if Necessary)	Filing Date March 17, 2004	Group Not Yet Assigned

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A	4,058,430	11/15/77	Suntola et al			
	B	4,413,022	11/1/83	Suntola et al			
	C	4,798,165	1/17/89	deBoer et al			
	D	5,006,363	4/9/91	Fujii et al			
	E	5,294,568	3/15/94	McNeilly et al			
	F	5,493,987	2/27/96	McDiarmid et al			
	G	5,648,321	7/15/97	Bednorz et al			
	H	5,773,078	6/30/98	Skelly			
	I	5,786,248	7/28/98	Schuegraf			
	J	5,830,277	11/3/98	Johnsgard et al			
	K	5,856,242	1/5/99	Arai et al			
	L	5,916,365	6/29/99	Sherman			
	M	5,964,949	10/12/99	Savas			
	N	5,968,279	10/19/99	MacLeish et al			
	O	5,972,430	10/26/99	Dimeo Jr et al			
	P	6,013,553	1/11/00	Wallace et al			
	Q	6,015,590	1/18/00	Suntola et al			
	R	6,037,235	3/14/00	Narwankar et al			
	S	6,118,100	9/12/00	Mailho et al			
	T	6,133,550	10/17/00	Griffiths et al			
	U	6,136,725	10/24/00	Loan et al			
	V	6,150,209	11/21/00	Sun et al			
	W	6,174,809	1/16/01	Kang et al			
	X	6,177,341	1/23/01	Lai			
	Y	6,198,074	3/6/01	Savas			
	Z	6,200,634	3/13/01	Johnsgard et al			
	AA	6,203,613	3/20/01	Gates et al			
	BB	6,207,583	3/27/01	Dunne et al			
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	DD	6,303,520	10/16/01	Kwong et al			
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	GG	6,342,691	1/29/02	Johnsgard et al			
	HH	6,342,777	1/29/02	Takahashi			
	II	6,355,909	3/12/02	Griffiths et al			
	JJ	6,420,279	7/16/02	Ono et al			
	KK	6,436,796	8/20/02	Mailho et al			
	LL	6,449,428	9/10/02	Aschner et al			
	MM	6,451,713	9/17/02	Tay et al			
	NN	6,531,793	2/13/03	Chang et al			
	OO	6,540,838	4/1/03	Sneh et al			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No
	PP							

Other Documents

Examiner		
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	QQ	D. Park et al, SiON/Ta2O5/TiN Gate Stack Transistor with 1.8nm Equivalent SiO2 Thickness, 1998, Tech Dig Int Electron Device Meet, P 381
	RR	Laun et al, Ultra Thin High Quality Ta2O5 Gate Dielectric Prepared By In Situ Rapid Thermal Processing, 1999, Tech Dig Int Electron Device Meet, 4 Pages
	SS	Wilk et al, Hafnium and Zirconium Silicates for Advanced Gate Dielectrics, 2000, Journal of Applied Physics, Vol 87(1), pp 484-492
	TT	Wilk et al, Stable Zirconium Silicate Gate Dielectrics Deposited Directly on Silicon, 1999, Applied Physics Letters, 76(1), pp 112-114
	UU	Denis et al, Model to Simulate Parabolic Followed by Linear Oxidation Kinetics, 1988, Oxidation of Metals, pp 153-167
	VV	Schuiskey et al, Atomic Layer Chemical Vapor Deposition of TiO2 Low Temperature Epitaxy of Rutile and Anatase, 2000, Journal of The Electrochemical Society, Vol 147(9), pp 3319-3325
	WW	PCT Search Report, 7/24/03
	XX	Buchan et al, Epitaxial Growth of GaAs with (C2H%)2GaCl and AsH3 in a Hot-Wall System, 1991, Journal of Crystal Growth 107, pp 331-336
	YY	Higashi et al, Sequential Surface Chemical Reaction Limited Growth of High Quality Al2O3 dielectrics
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.